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Supporting Information

Solution-Processed Vanadium Oxide as an Efficient Hole Injection layer for Quantum-Dot Light-Emitting Diodes

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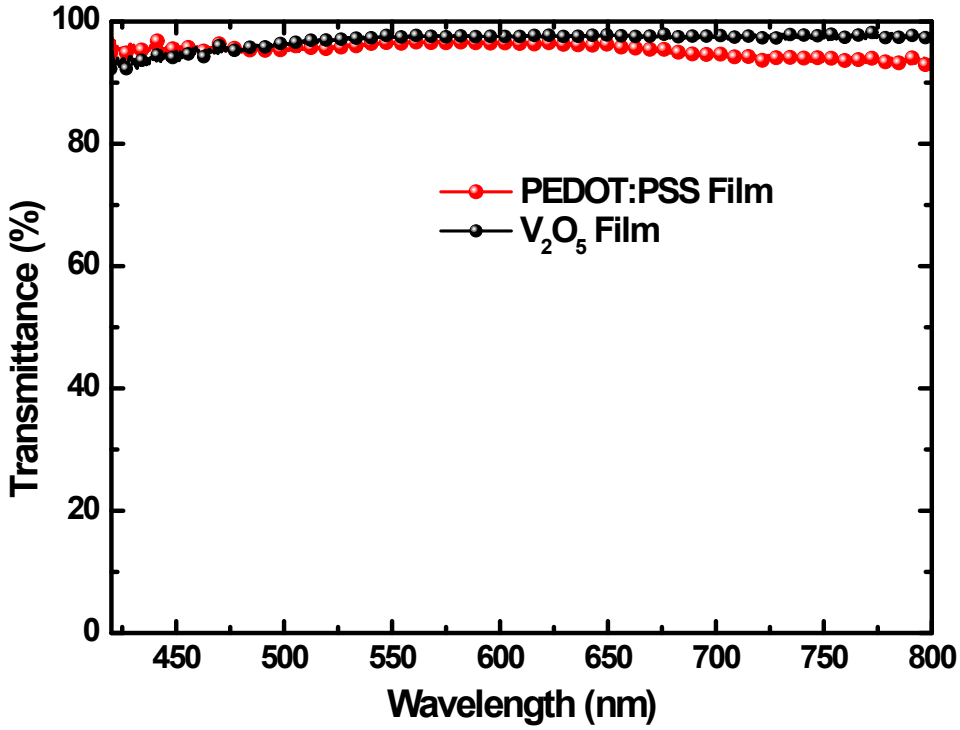

Figure S1. the transmittance of the V_2O_5 and PEDOT:PSS film.

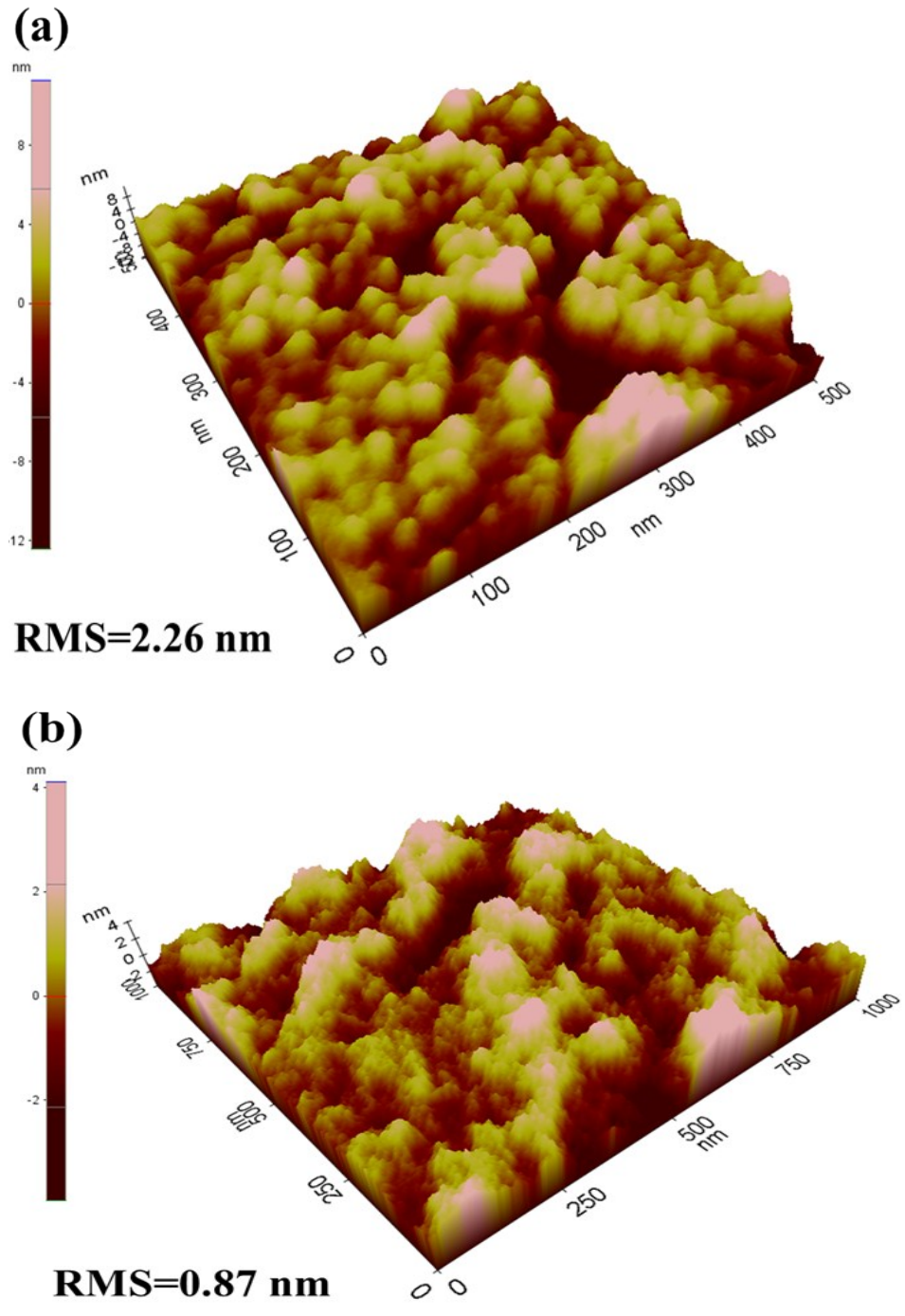

Figure S2. AFM images of (a) solution-processed V_2O_5 and (b) PEDOT:PSS films on the Glass/ITO substrate.

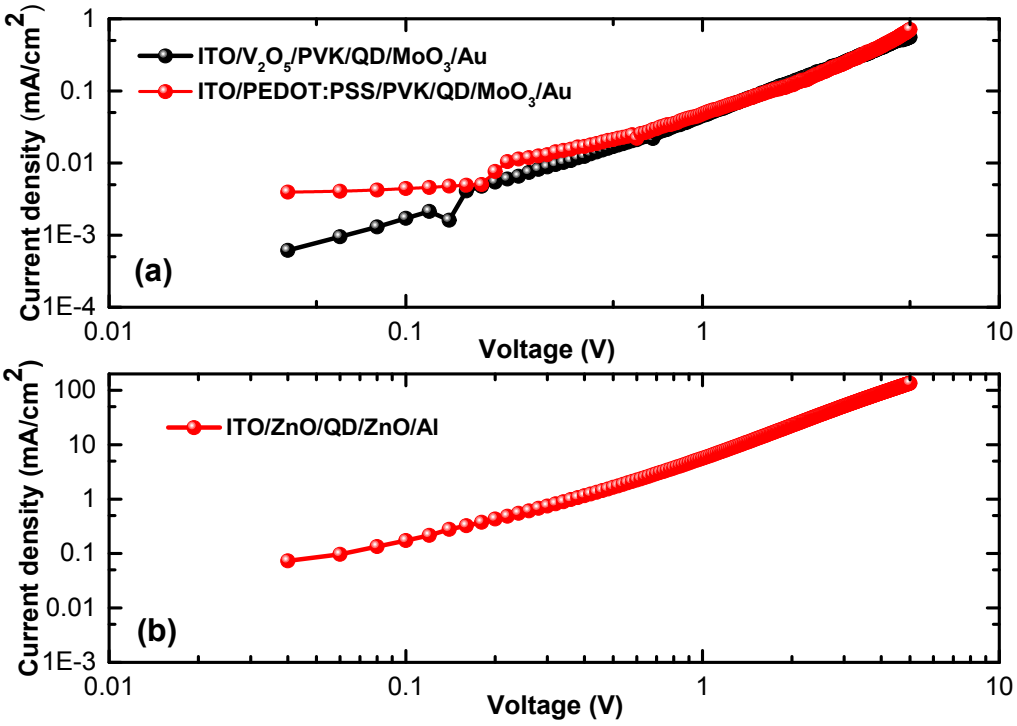

Figure S3. J−V characteristics of the hole-only devices (a) and electron-only devices (b). (In the hole-only devices, the thicknesses of PEDOT:PSS, PVK, QD and V_2O_5 (1:250) are identical to those used in the QLED devices. And the thickness of MoO_3 and Au are 25 nm and 80 nm, respectively. In the electron-only devices, the thickness of ZnO and QD are the same as those used in the QLEDs.)

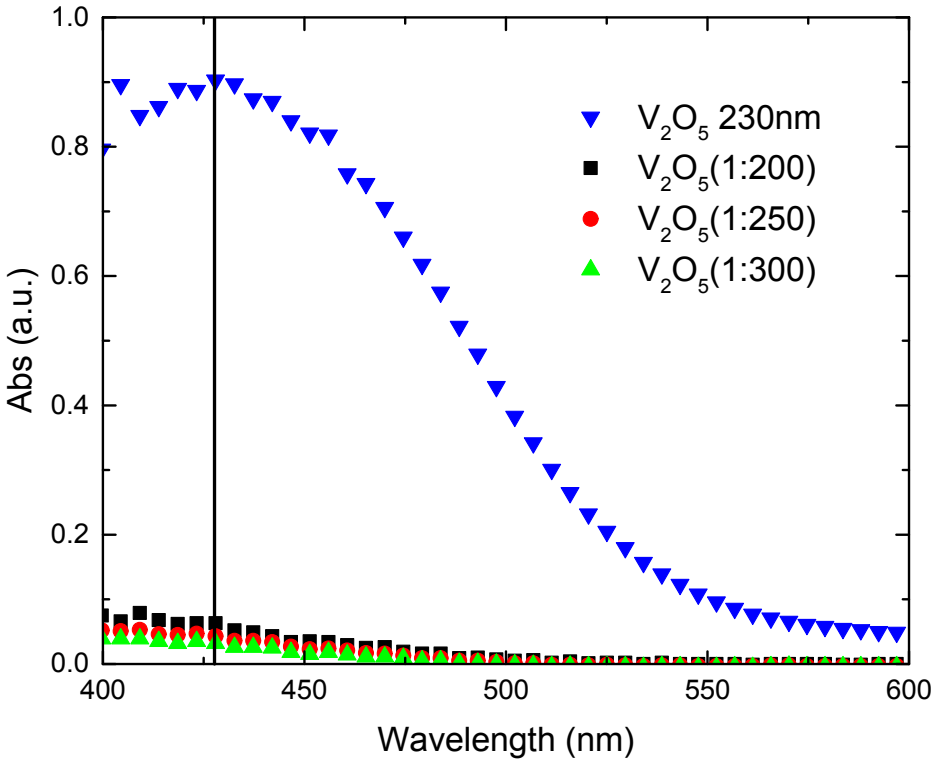

Figure S4. The absorbance of the V_2O_5 film with different thickness.